

IN THE CLAIMS:

Please amend claims 1-3, 5-7, 10-11, and 13 as follows:

1. (Twice Amended) An interlevel dielectric structure comprising:

a single first dielectric layer situated on a semiconductor substrate, said single first dielectric layer having an upper surface;

a plurality of lines comprised of a single conductive material extending along said upper surface of said single first dielectric layer, each line of said plurality of lines having upper and lower surfaces, and adjacent lines of said plurality of lines having spaces situated therebetween, the lower surfaces of each line of said plurality of lines being in contact with said upper surface of said single first dielectric layer;

a single second dielectric layer above both said plurality of lines and said single first dielectric layer, said single second dielectric layer having a lower surface in contact with the upper surface of each line of said plurality of lines; and

a single dielectric material situated in said space between adjacent lines of said plurality of lines, said single dielectric material not extending over the upper surface of each line of said plurality of lines, the upper surface of said single dielectric material being higher than the upper surface of each line of said plurality of lines, the lower surface of said single dielectric material being lower than the lower surface of each line of said plurality of lines.

2. (Once Amended) The interlevel dielectric structure as defined in Claim 1, wherein

the dielectric material comprises PTFE.

3. (Once Amended) The interlevel dielectric structure as defined in Claim 1, wherein at least one of the single first dielectric layer and single second dielectric layer comprises silicon dioxide.

5. (Once Amended) The interlevel dielectric structure as defined in Claim 1, where the single dielectric material has a dielectric constant of less than about 3.6.

6. (Twice Amended) An interlevel dielectric structure comprising:

a single first dielectric layer situated on a semiconductor substrate, said single first dielectric layer having an upper surface;

a plurality of lines comprised of a conductive material extending along said upper surface of said single first dielectric layer; wherein:

each line of said plurality of lines has an upper surface, a lower surface, and at least one side surface;

adjacent lines of said plurality of lines have spaces situated therebetween;

the lower surfaces of each line of said plurality of lines is in contact with said upper surface of said single first dielectric layer; and

the upper surface of at least one line of said plurality of lines has thereon a layer of a refractory metal nitride;

a single second dielectric layer above both said plurality of lines and said single first dielectric layer, said single second dielectric layer having a lower surface in contact with the upper surface of each line of said plurality of lines; and

a single dielectric material situated in said space between adjacent lines of said plurality of lines, said single dielectric material not extending over the upper surface of each line of said plurality of lines, the upper surface of said single dielectric material being higher than the upper surface of each line of said plurality of lines, the lower surface of said single dielectric material being lower than the lower surface of each line of said plurality of lines.

7. (Twice Amended) The interlevel dielectric structure as defined in Claim 6, wherein:
said layer of refractory metal nitride has an electrical insulation layer thereon, said
electrical insulation layer having thereon said single second dielectric layer; and
at least one side surface of the single dielectric material is in contact with at least one
side surface of at least one of the plurality of lines.

10. (Once Amended) The interlevel dielectric structure as defined in Claim 6, wherein
said single dielectric material comprises PTFE.

11. (Once Amended) The interlevel dielectric structure as defined in Claim 6, wherein at
least one of the single first dielectric layer and single second dielectric layer [layers] comprises
silicon dioxide.

13. (Once Amended) The interlevel dielectric structure as defined in Claim 6, where the
single dielectric material has a dielectric constant of less than about 3.6.